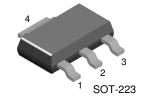


## **BSP52**

# **NPN Darlington Transistor**

- This device is designed for applications requiring extremly high current gain at collector currents to 500mA.
- Sourced from process 03.



1. Base 2. Collector 3. Emitter

# **Absolute Maximum Ratings\*** $T_A=25$ °C unless otherwise noted

| Symbol                            | Parameter  | Value       | Units |
|-----------------------------------|--|-------------|-------|
| V <sub>CES</sub>                  | Collector-Emitter Voltage                        | 80          | V     |
| V <sub>CBO</sub>                  | Collector-Base Voltage                           | 90          | V     |
| V <sub>EBO</sub>                  | Emitter-Base Voltage                             | 5           | V     |
| I <sub>C</sub>                    | Collector Current - Continuous                   | 800         | mA    |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Junction Temperature Range | - 55 ~ +150 | °C    |

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- NOTES:

  1) These ratings are based on a maximum junction temperature of 150°C.

  2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Electrical Characteristics T<sub>A</sub>=25°C unless otherwise noted

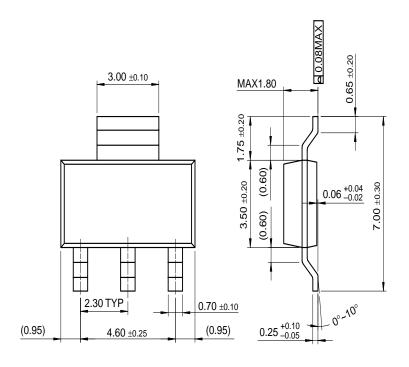
| Symbol                | Parameter                            | Test Conditions                               | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|---|------|------|------|-------|
| Off Charac            | Off Characteristics                  |   |      |      |      |       |
| V <sub>(BR)CBO</sub>  | Collector-Base Breakdown Voltage     | $I_C = 100 \mu A, I_E = 0$                    | 90   |      |      | V     |
| V <sub>(BR)EBO</sub>  | Emitter-Base Breakdown Voltage       | $I_E = 10\mu A, I_C = 0$                      | 5    |      |      | V     |
| I <sub>CES</sub>      | Collector Cutoff Current             | $V_{CE} = 80V, V_{BE} = 0$                    |      |      | 10   | μΑ    |
| I <sub>EBO</sub>      | Emitter Cutoff Current               | $V_{EB} = 4.0V, I_{C} = 0$                    |      |      | 10   | μΑ    |
| On Characteristics    |                                      |   |      |      |      |       |
| h <sub>FE</sub>       | DC Current Gain                      | I <sub>C</sub> = 150mA, V <sub>CE</sub> = 10V | 1000 |      |      |       |
|                       |                                      | $I_C = 500 \text{mA}, V_{CE} = 10 \text{V}$   | 2000 |      |      |       |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | $I_C = 500 \text{mA}, I_B = 0.5 \text{mA}$    |      |      | 1.3  | V     |
| V <sub>BE</sub> (sat) | Base-Emitter Saturation Voltage      | $I_C = 500 \text{mA}, I_B = 0.5 \text{mA}$    |      |      | 1.9  | V     |

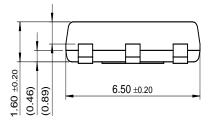
# Thermal Characteristics $T_A=25$ °C unless otherwise noted

| Symbol          | Parameter                               | Max. | Units |
|-----------------|---|------|-------|
| P <sub>D</sub>  | Total Device Dissipation                | 1000 | mW    |
|                 | Derate above 25°C                       | 8.0  | mW/°C |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 125  | °C/W  |

# **Package Demensions**

# **SOT-223**





Dimensions in Millimeters

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| DOME™                | HiSeC™              | Power247™                | SuperSOT™-6           |            |
| EcoSPARK™            | I <sup>2</sup> C™   | PowerTrench <sup>®</sup> | SuperSOT™-8           |            |
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| EnSigna™             | LittleFET™          | QS™                      | TinyLogic™            |            |
| FACT™                | MicroFET™           | QT Optoelectronics™      | TruTranslation™       |            |
| FACT Quiet series™   | MicroPak™           | Quiet Series™            | UHC™                  |            |
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|--------------------------|---------------------------|---|
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